

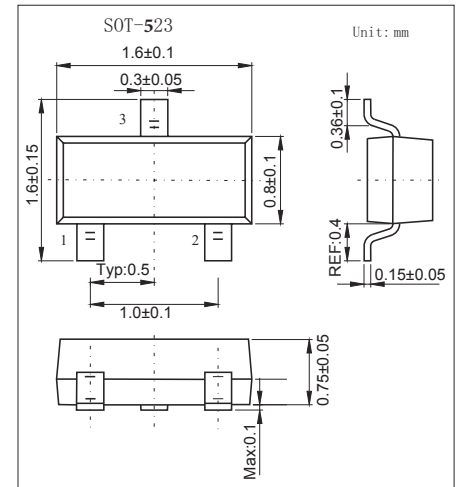
SOT-23 Plastic-Encapsulate MOSFETS

FEATURE

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for Portable equipment
- Easily designed drive circuits
- Easy to parallel
- N-channel MOSFET

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current	0.1	A
R _{θJA}	Thermal Resistance, Junction-to-Ambient	833	°C /W
P _D	Power Dissipation	0.15	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

V _{(BR)DSS}	R _{DS(on)MAX}	I _D
30V	8Ω@4V	100mA
	13Ω@2.5V	

MOSFET ELECTRICAL CHARACTERISTICS T_a = 25 °C unless otherwise specified

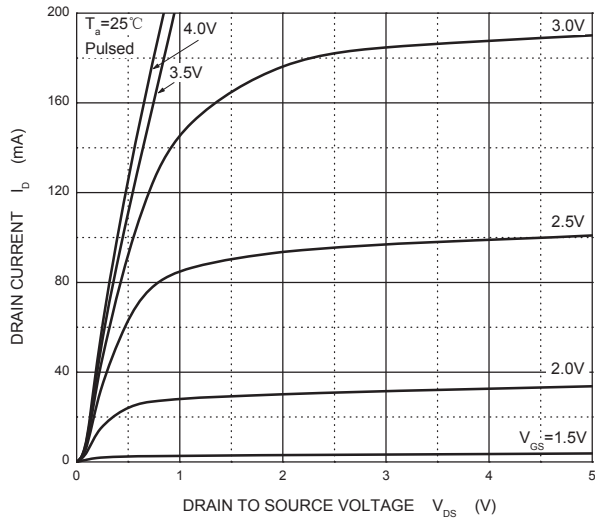
Parameter	Symbol	Test Condition	Min	Typ	Max	Units	
Off Characteristics							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0V, I _D = 10μA	30			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V			1	μA	
Gate -Source leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±2	μA	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = 3V, I _D = 100μA	0.8		1.5	V	
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 4V, I _D = 10mA			8	Ω	
		V _{GS} = 2.5V, I _D = 1mA			13	Ω	
Forward Transconductance	g _{FS}	V _{DS} = 3V, I _D = 10mA	20			mS	
Dynamic Characteristics*							
Input Capacitance	C _{iss}	V _{DS} = 5V, V _{GS} = 0V, f = 1MHz		13		pF	
Output Capacitance	C _{oss}				9		pF
Reverse Transfer Capacitance	C _{rss}				4		pF
Switching Characteristics*							
Turn-On Delay Time	t _{d(on)}	V _{GS} = 5V, V _{DD} = 5V, I _D = 10mA, R _g = 10Ω, R _L = 500Ω,		15		ns	
Rise Time	t _r			35		ns	
Turn-Off Delay Time	t _{d(off)}			80		ns	
Fall Time	t _f			80		ns	

* These parameters have no way to verify.

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

Output Characteristics



Transfer Characteristics

